## Code: 7GC24

| B.Tech. || Semester Supplementary Examinations December 2022

## Engineering Mathematics-II

(Common to All Branches)
Time: 3 Hours
Max. Marks: 70
Answer any five full questions by choosing one question from each unit ( $5 \times 14=70$ Marks )

1. Change the order of integration in $\int_{0}^{1 \sqrt{2-x^{2}}} \frac{x}{\sqrt{x^{2}+y^{2}}} d y d x$ and hence evaluate it.

## OR

2. a) Change of order of integration and evaluate $\int_{0}^{\infty} \int_{x}^{\infty} \frac{e^{-y}}{y} d x d y$
b) Evaluate $\int_{0}^{a} \int_{0}^{x+y} \int_{0}^{x+y} e^{x+y+z} d z d y d x$

## UNIT-II

3. a) Evaluate $\int_{0}^{\infty} e^{-2 t} \operatorname{Sin}^{3} t d t$
b) Obtain the Laplace Transform of $f(t)=\left\{\begin{array}{cc}(t-1)^{2} & ; t>1 \\ 0 & ; 0<t<1\end{array}\right.$

OR
4. a) Find the Laplace Transform of $\frac{\operatorname{Cos} a t-\operatorname{Cos} b t}{t}$
b) Find the Laplace Transform of $t^{2} e^{-3 t}$.

UNIT-III
5. Using Convolution Theorem, Find $L^{-1}\left\{\frac{s^{2}}{\left(s^{2}+4\right)\left(s^{2}+9\right)}\right\}$

> OR
6. a) Find the inverse transform of $\frac{1}{s\left(s^{2}+a^{2}\right)}$.
b) Find the inverse transform of $\frac{s+2}{s^{2}-4 s+13}$ UNIT-IV.
7. Show the vector $\left(x^{2}-y z\right) \bar{i}+\left(y^{2}-z x\right) \bar{j}+\left(z^{2}-x y\right) \bar{k}$ is irrotational and find it's scalar potential.
8. a) Evaluate curl of $\bar{V}=e^{x y z}(\bar{i}+\bar{j}+\bar{k})$ at the point $(1,2,3)$.
b) Prove that $\operatorname{div} \operatorname{curl} \bar{F}=0$

## UNIT-V

9. Verify Green's Theorem in the plane for $\int_{c}\left[\left(3 x^{2}-8 y^{2}\right) d x+(4 y-6 x y) d y\right]$ where ' $c$ ' encloses the region bounded by $y=\sqrt{x}$ and $y=x^{2}$

## OR

10. Verify stoke's theorem for a vector field $\bar{F}=\left(x^{2}+y^{2}\right) \bar{i}-2 x y \bar{j}$ taken round the rectangle bounded by the lines $x= \pm a, y=0, y=b$.
Hall Ticket Number :
R-17
Code: 7GC22| B.Tech. || Semester Supplementary Examinations December 2022
Engineering Chemistry
(Common to EEE \& ECE)
Time: 3 Hours Max. Marks: 70
Answer any five full questions by choosing one question from each unit ( $5 \times 14=70$ Marks )
$* * * * * * * * *$
Marks
UNIT-I
11. a) Describe the estimation of hardness of water by EDTA method. ..... 8M
b) What are boiler troubles? Describe scale and sludge. ..... 6 M
OR
12. Describe the process of water treatment by ion exchange method.14M
UNIT-II
13. a) Differentiate the Primary and secondary batteries ..... 7M
b) Describe the chemistry of Dry Cell. ..... 7M
OR
14. a) Write short notes on i) electrode ii) electrolyte iii) salt bridge. ..... 6M
b) What are conductometric titrations? Describe strong acid Vs Strong base titration. ..... 8M
UNIT-III
15. a) Illustrate the conducting mechanism of poly-acetylene ..... 7M
b) Discuss the differences between Thermoplastics and Thermo settings ..... 7M
OR
16. Describe the processing of Natural rubber. What are its disadvantages? ..... 14M
UNIT-IV
17. a) Explain the process of Flue gas analysis by Orsat's apparatus. ..... 7M
b) Write a note on a) Octane Number b) b) Cetane Number. ..... 7M
OR
18. Describe the manufacture of Coke by Otto Hoffmann by product Oven. Also explain the recovery of by products. ..... 14M
UNIT-V9. Describe the manufacture of Portland cement.14 M
OR
19. a) What are lubricants Describe any two properties of lubricants. ..... 7 M
b) Define refractories. Describe their classification with examples. ..... 7 M

## Code: 7G523

| B.Tech. || Semester Supplementary Examinations December 2022

## Geometrical Drawing

(Common to EEE \& ECE)
Max. Marks: 70
Time: 3 Hours
Answer any five full questions by choosing one question from each unit ( $5 \times 14=70$ Marks )

## UNIT-I

1. a) Construct a regular Hexagon of given side 30 mm .
b) Divide a given line of 75 mm long in to TEN equal parts

OR
2. Construct a cycloid having a rolling circle diameter as 50 mm . Also draw a normal and a tangent to a curve at a point 35 mm above the base line.

## UNIT-II

3. A line $A B$ of 50 mm long is parallel to both H.P and V.P. The line is 40 mm above H.P and 30 mm in front of V.P. Draw the projections of the line.

## OR

4. One end $A$ of a line $A B, 75 \mathrm{~mm}$ long is 20 mm above the H.P. and 25 mm in front of the V.P. The line is inclined at $30^{\circ}$ to the H.P. and the top view makes $45^{\circ}$ with the V.P. Draw the projections of the line and find the true inclinations with the vertical plane.

## UNIT-III

5. An equilateral triangular plane ABC of 30 mm side is parallel to V.P \& perpendicular to H.P and 25 mm away from V.P. Draw its projections when one of its sides is (i) Parallel to H.P (ii) Perpendicular to H.P (iii) inclined at $45^{\circ}$ to the HP.

## OR

6. A square plane of side 40 mm has its surface parallel to VP and perpendicular to HP .

Draw its projections when one of the sides is inclined at $30^{\circ}$ to HP.

## UNIT-IV

7. A cylinder of base diameter 40 mm and axis 70 mm long lies on a point of its base such that its axis is $30^{\circ}$ inclined to HP and $45^{\circ}$ to VP. Draw its projections.

## OR

8. Draw the projections of a cone of base 30 mm diameter and axis 50 mm long, when it is resting on HP on its base.

## UNIT-V

9. Draw the isometric projection of a circle of diameter 50 mm with its plane horizontal and vertical

OR
10. Convert the following orthographic view in to isometric view as shown in Fig. 2


Fig. 2 ( All dimensions are in 'mm')
Hall Ticket Number :
R-17
Code: 7G121| B.Tech. I| Semester Supplementary Examinations December 2022
Data Structures(Common to All Branches)Time: 3 Hours
Max. Marks: 70
Answer any five full questions by choosing one question from each unit ( $5 \times 14=70$ Marks )
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UNIT-I1. a) Write a program to perform addition of array elements using pointer to array.7M
b) Explain the declaration of pointers and pointer to pointer with examples. ..... 7M
OR2. a) Explain dynamic memory allocation functions in C in detail.7M
b) What is the use of command line arguments ..... 7M
UNIT-II3. a) Write a program for sorting given numbers using selection sort technique7M
b) Write an algorithm for Binary search? Validate it with suitable data set? ..... 7M
OR
4. Write a C program that defines a structure employee containing the details such asempno, empname, department name and salary. The structure has to store 20employees in an organization. Use the appropriate method to define the above detailsand define a function that will display the contents?14M
UNIT-III5. Write an algorithm to convert a given infix expression into prefix expression.
OR6. Write a C Program to perform the following operations on a queue
a) Insert b) Delete ..... 14M
UNIT-IV7. What is a Circular Linked List.? Explain different operations of a Circular linked list withsuitable examples.14M
OR
8. What are different types of linked list? Write a C function to count number of elementspresent in single linked list.14 M
UNIT-V
9. State binary search tree property. And construct the binary search tree for the following keys: G, K, L, R, A, C, T, F, J, T, Y, E.

## OR

10. Define Graph and describe various representations of a graph with suitable examples.

# Hall Ticket Number : 

## R-17

## Code: 7G321

| B.Tech. || Semester Supplementary Examinations December 2022

## Electronic Devices and Circuits

## (Common to EEE \& ECE)

Max. Marks: 70
Time: 3 Hours
Answer any five full questions by choosing one question from each unit ( $5 \times 14=70$ Marks )
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## UNIT-I

1. Design a fixed bias circuit and explain why this circuit is unstable, if the transistor is replaced by another of the same type?

OR
2. a) Draw a voltage divider bias circuit and derive an expression for its stability factor.
b) Name the different types of biasing circuits and give three circuit configurations.

## UNIT-II

3. Explain the principle of MOSFET in depletion mode with neat sketches and output characteristics.

## OR

4. a) Design a source bias circuit of JFET and explain how it is going to provide solid Q-point with current source bias.
b) Design a biasing circuit for depletion type MOSFET with required parameters and compare the same with enhancement type MOSFET.

## UNIT-III

5. Draw the circuit diagram of common base amplifier and derive the expressions for current gain and voltage gain.

## OR

6. a) With a neat circuit diagram, explain the working of a transistor amplifier.
b) Discuss the merits and limitations of common base amplifier.

## UNIT-IV

7. Design a source follower circuit with $\mathrm{Rg}=100 \mathrm{M}$, $\mathrm{Rs}=10 \mathrm{k}$ and $\mathrm{gm}=8000 \mu \mathrm{~s}$. and also find the input and output resistance of the circuit.

## OR

8. a) A FET amplifier has $\mathrm{gm}=2.5 \mathrm{~mA} / \mathrm{V}$ and $\mathrm{rd}=500 \mathrm{k}$. The load resistance is 10 k .find the value of voltage gain.
b) What are the advantages of FET amplifier over BJT amplifier?

## UNIT-V

9. a) What is a UJT? How does it differ from FET?

$$
\begin{aligned}
& \text { b) The } 2 N 5431 \text { UJT has a rating of } \eta=0.8(\max ) \text {. Determine the maximum value of } \mathrm{Vp} \text { for the } \\
& \text { device when it is being used in the circuit with } \mathrm{V}_{B B}=+18 \mathrm{~V} \text {. take } \mathrm{V}_{\mathrm{D}}=0.7 \mathrm{~V} \text {. }
\end{aligned}
$$

10. a) What is the working principles of schotkey diode?
b) Write a note on LED.
